

15N25

UNISONIC TECHNOLOGIES CO., LTD

Preliminary

15A, 250V N-CHANNEL POWER MOSFET

DESCRIPTION

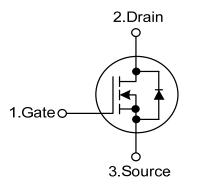
The UTC 15N25 is an N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect ${\sf R}_{{\sf DS}({\sf ON})},$ high switching speed, high current capacity and low gate charge.

The UTC **15N25** is universally applied in low voltage such as automotive, high efficiency switching for DC/DC converters and DC motor control, etc.

FEATURES

- * R_{DS(ON)}<0.32Ω @ V_{GS}=10V, I_D=7.5A
- * High Switching Speed



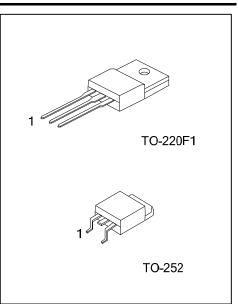


ORDERING INFORMATION

Ordering Number		Deekege	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
15N25L-TF1-T	15N25G-TF1-T	TO-220F1	G	D	S	Tube	
15N25L-TN3-T	25L-TN3-T 15N25G-TN3-T		G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source

15N25L-TF1-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube, R: Tape Reel (2) TF1: TO-220F1, TN3: TO-252 (3) L: Lead Free, G: Halogen Free and Lead Free
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ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	250	V
Gate-Source Voltage		V _{GSS}	±30	V
Continuous Drain Current	Continuous	I _D	15	А
	Pulsed	I _{DM} 60		А
Single Pulsed Avalanche Current		I _{AS}	15	А
Single Pulsed Avalanche Energy		E _{AS}	170	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.0	V/ns
Power Dissipation	TO-220F1	D	25	W
	TO-252	P _D	85	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. L=1.58mH, I_{AS}=15A, V_{DD}=50V, R_G=25 Ω , Starting T_J = 25°C

4. $I_{SD} \le 15A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220F1	0	62.5	°C/W	
	TO-252	θ _{JA}	110	°C/W	
Junction to Case	TO-220F1	θ _{JC}	5	°C/W	
	TO-252		1.47	°C/W	



ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	IYP	MAX	UNII
OFF CHARACTERISTICS			250	1		
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V				V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =250V, V _{GS} =0V			1	μA
Gate-Source Leakage Current		V _{GS} =+30V, V _{DS} =0V			+100	nA
Reverse	I _{GSS}	V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250µA	2		4	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7.5A			0.32	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		830		рF
Output Capacitance	C _{OSS}			200		рF
Reverse Transfer Capacitance	C _{RSS}			25		рF
SWITCHING PARAMETERS		_				
Total Gate Charge	Q_{G}	V _{GS} =10V, V _{DD} =50V, I _D =1.3A		67		nC
Gate to Source Charge	Q _{GS}			15		nC
Gate to Drain Charge	Q_{GD}			18		nC
Turn-ON Delay Time	t _{D(ON)}			40		ns
Rise Time	t _R	V _{DD} =30V, I _D =0.5A, R _G =25Ω, V _{GS} =10V		50		ns
Turn-OFF Delay Time	t _{D(OFF)}			130		ns
Fall-Time	t _F			50		ns
SOURCE- DRAIN DIODE RATINGS AND	CHARACTER	RISTICS				
Maximum Body-Diode Continuous					15	٨
Current	I _S				15	A
Maximum Body-Diode Pulsed Current	I _{SM}				60	Α
Drain-Source Diode Forward Voltage	V _{SD}	I _S =15A, V _{GS} =0V			1.5	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =15A, V _{GS} =0V, dI _F /dt=100A/µs		190		ns
Reverse Recovery Charge	Qrr	(Note 1)		1.3		μC



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